

Title (en)  
METHOD FOR PRODUCING A SILICIUM CAPACITOR

Title (de)  
VERFAHREN ZUR HERSTELLUNG EINES SILIZIUMKONDENSATORS

Title (fr)  
PROCEDE DE PRODUCTION D'UN CONDENSATEUR AU SILICIUM

Publication  
**EP 0963601 A1 19991215 (DE)**

Application  
**EP 98905245 A 19980112**

Priority  
• DE 9800089 W 19980112  
• DE 19701935 A 19970121

Abstract (en)  
[origin: DE19701935C1] The invention relates to method for producing a silicium capacitor by producing hole structures (2) on a silicium substrate (1). A conductive area (3) is produced in the surface of said structures by doping, to which a dielectric layer (4) and a conducting layer (5) is applied without filling the hole structures (2). In order to compensate the mechanical stress of the silicium substrate (1) caused by the doping of the conductive area (3), a conformal auxiliary layer (6) is formed on the surface of the conducting layer (5), which is subjected to compressive mechanical tension

IPC 1-7  
**H01L 21/3205**

IPC 8 full level  
**H01L 27/04** (2006.01); **H01L 21/334** (2006.01); **H01L 21/822** (2006.01); **H01L 29/94** (2006.01); **H10B 12/00** (2023.01)

CPC (source: EP KR US)  
**H01L 21/3205** (2013.01 - KR); **H01L 29/66181** (2013.01 - EP US); **H10B 12/038** (2023.02 - EP US); **Y10S 438/96** (2013.01 - EP US)

Designated contracting state (EPC)  
AT CH DE DK ES FI FR GB IE IT LI NL SE

DOCDB simple family (publication)  
**DE 19701935 C1 19971211**; EP 0963601 A1 19991215; JP 2001508948 A 20010703; KR 20000070287 A 20001125; TW 370705 B 19990921; US 6165835 A 20001226; WO 9832166 A1 19980723

DOCDB simple family (application)  
**DE 19701935 A 19970121**; DE 9800089 W 19980112; EP 98905245 A 19980112; JP 53351598 A 19980112; KR 19997006516 A 19990719; TW 86119961 A 19971230; US 34193799 A 19990720